

GSE050LB1D3F

ESD Protection Diode

Product Description

It is designed to protect sensitive electronics from damage due to electrostatic discharge (ESD) and other transient events.

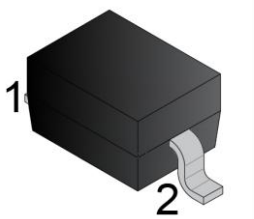
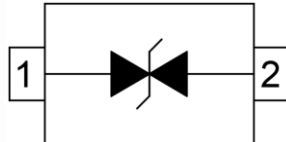
Features

- Operating Voltage: 5V
- IEC61000-4-2(ESD) $\pm 30\text{kV}$ (Air)
- IEC61000-4-2(ESD) $\pm 30\text{kV}$ (Contact)
- IEC61000-4-5 (Lightning) 8A (8/20 μs).

Mechanical Data

- SOD-323. Package
- RoHS Compliant and Halogen Free

Package and Pin Assignment

SOD-323	Equivalent Circuit
	

Ordering and Marking Information

GS P/N	Package	Marking	Quantity / Reel
GSE050LB1D3F	SOD-323	B5	3,000PCS
GSE050LB1D3F - Product Code: GSE050LB1 - Package Code: D3 for SOD-323 - Green Level: F for RoHS Compliant and Halogen Free			
Marking Information			
<div style="border: 1px solid black; padding: 5px; display: inline-block;">B5</div>		- Product Code: B5	

Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Symbol	Parameter	Value	Unit
P _{PP}	Peak Pulse Power (t _p =8/20μs)	100	W
I _{PP}	Peak Pulse Current (t _p =8/20μs)	8	A
V _{ESD}	ESD Per IEC61000-4-2 (Air)	±30	KV
	ESD Per IEC61000-4-2 (Contact)	±30	KV
T _J	Operating Junction Temperature Range	-55 to +125	°C
T _{STG}	Storage Temperature Range	-55 to +150	°C
T _L	Lead Soldering Temperature	260 (10 sec.)	°C

Electrical Characteristics (T_A=25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{RWM}	Reverse Working Voltage	-			5	V
V _{BR}	Breakdown Voltage	I _T = 1mA	5.6			V
I _R	Reverse Leakage Current	V _{RWM} =5V			0.2	μA
V _C	Clamping Voltage	I _{PP} =1A (8/20μs)			8	V
		I _{PP} =8A (8/20μs)			13	V
C _J	Junction Capacitance	V _R =0V, f=1MHz		18	25	pF

Electrical Parameters

Symbol	Parameter	
I _{PP}	Reverse Peak Pulse Current	
V _C	Clamping Voltage @ I _{PP}	
V _{RWM}	Reverse Stand-Off Voltage	
I _R	Reverse Leakage Current @ V _{RWM}	
V _{BR}	Breakdown Voltage @ I _T	
I _T	Test Current	

Typical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise specified)

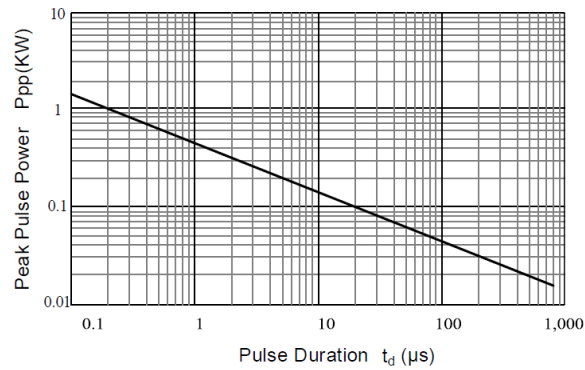


Fig 1. Peak Pulse Power vs. Pulse Time

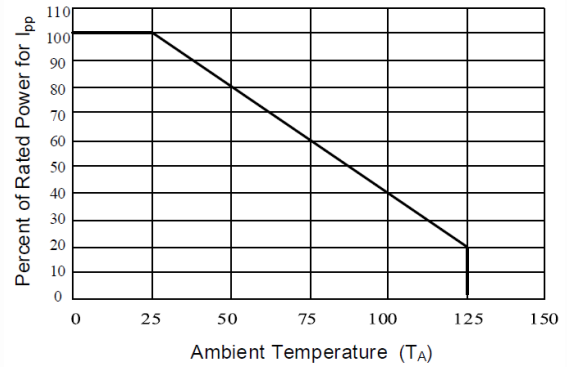


Fig 2. Power Derating Curve

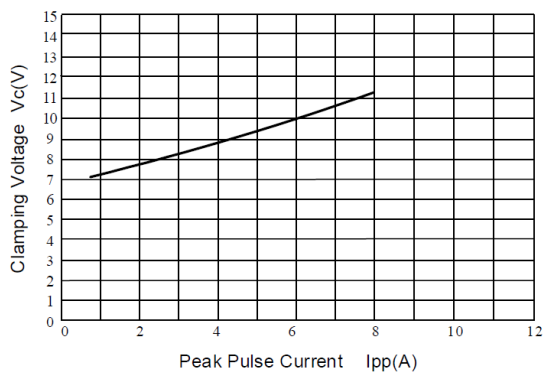


Fig 3. Clamping Voltage vs. Peak Pulse Current

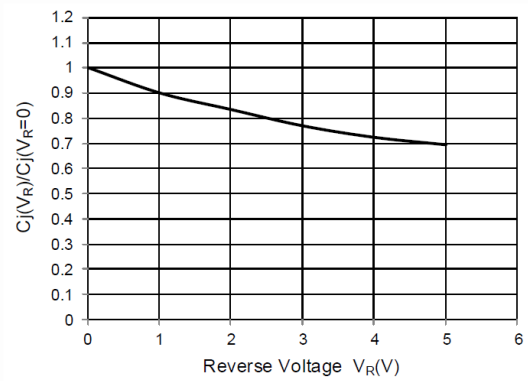


Fig 4. Junction Capacitance vs. Reverse Voltage

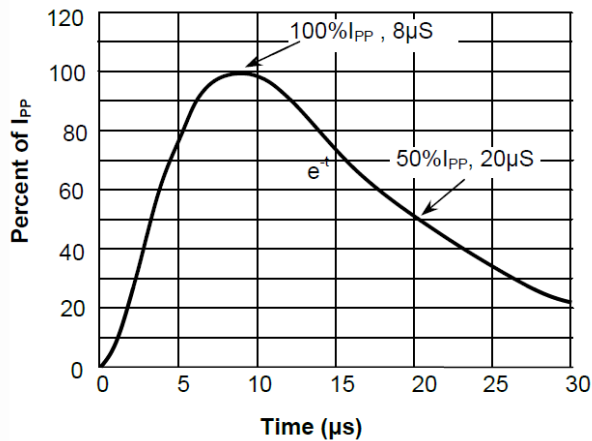


Fig 5. 8 X 20μs Pulse Waveform

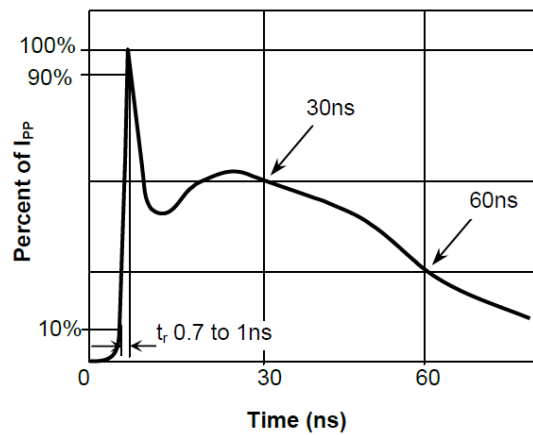
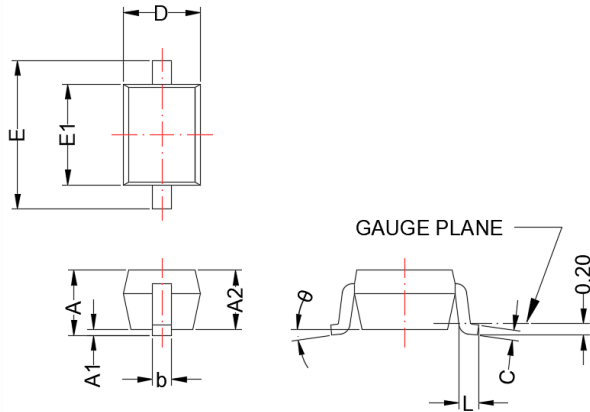


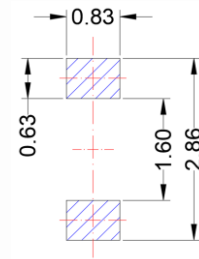
Fig 6. ESD(IEC61000-4-2) Pulse Waveform

SOD-323

Package Dimension



Recommended Land Pattern



Unit:mm

Dimensions				
Symbol	Millimeters		Inches	
	MIN	MAX	MIN	MAX
A	---	1.16	---	0.046
A1	0.00	0.14	0.000	0.006
A2	0.80	---	0.031	---
b	0.25	0.40	0.010	0.016
C	0.08	0.25	0.003	0.010
D	1.15	1.40	0.045	0.055
E	2.30	2.80	0.091	0.110
E1	1.40	1.80	0.055	0.071
L	0.08	---	0.003	---
θ	0°	8°	0°	8°





NOTE:



Dimensions are exclusive of Burrs, Mold Flash & Tie Bar extrusions.

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